

ABSTRACT OF THE DISCLOSURE

A first amplifier amplifies voltage of a first local bit line connected to static memory cells. Precharging circuits for precharging a first global bit line connected to an output of the first amplifier supply a precharging current through both ends of the first global bit line,
5 respectively. Since the precharging current flows through the first global bit line in both directions, electromigration criteria can be made looser than in cases where the current flows in one direction. This makes it possible to avoid a defect which occurs due to electromigration of the first global bit line. Since the first global bit line can be reduced in wiring width, it is possible to minimize the layout area. As a result, the semiconductor
10 memory can be reduced in chip size with a reduction in chip cost.